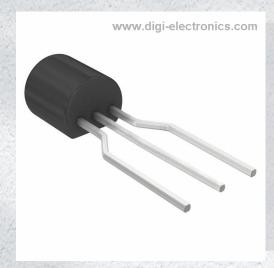


2N4403RLRAG Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number

2N4403RLRAG-DG

Manufacturer

onsemi

Manufacturer Product Number

2N4403RLRAG

Description

TRANS PNP 40V 0.6A TO92

Detailed Description

Bipolar (BJT) Transistor PNP 40 V 600 mA 200MHz 6

25 mW Through Hole TO-92 (TO-226)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
2N4403RLRAG	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
PNP	600 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, Ic:
40 V	750mV @ 50mA, 500mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
	100 @ 150mA, 2V
Power - Max:	Frequency - Transition:
625 mW	200MHz
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-226-3, TO-92-3 Long Body (Formed Leads)	TO-92 (TO-226)
Base Product Number:	
2N4403	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
FΔRQQ	8541 21 0075

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Preferred Device

General Purpose Transistors

PNP Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	40	Vdc
Collector – Base Voltage	V _{CBO}	40	Vdc
Emitter – Base Voltage	V _{EBO}	5.0	Vdc
Collector Current – Continuous	I _C	600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

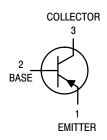
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

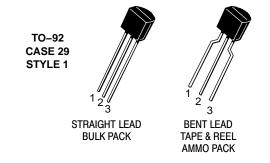
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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MARKING DIAGRAM



2N4403 = Device Code A = Assembly Location

Y = Year WW = Work Week ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic			Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•		•	
Collector-Emitter Breakdown	Voltage (Note 1)	$(I_C = 1.0 \text{ mAdc}, I_B = 0)$	V _{(BR)CEO}	40	_	Vdc
Collector-Base Breakdown V	oltage	$(I_C = 0.1 \text{ mAdc}, I_E = 0)$	V _{(BR)CBO}	40	-	Vdc
Emitter-Base Breakdown Vol	tage	$(I_E = 0.1 \text{ mAdc}, I_C = 0)$	V _{(BR)EBO}	5.0	-	Vdc
Base Cutoff Current		$(V_{CE} = 35 \text{ Vdc}, V_{EB} = 0.4 \text{ Vdc})$	I _{BEV}	-	0.1	μAdc
Collector Cutoff Current		(V _{CE} = 35 Vdc, V _{EB} = 0.4 Vdc)	I _{CEX}	-	0.1	μAdc
ON CHARACTERISTICS						
DC Current Gain		$ \begin{array}{c} (I_C=0.1 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_C=1.0 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_C=10 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_C=10 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_C=500 \text{ mAdc, } V_{CE}=2.0 \text{ Vdc}) \text{ (Note 1)} \\ (I_C=500 \text{ mAdc, } V_{CE}=2.0 \text{ Vdc}) \text{ (Note 1)} \end{array} $	h _{FE}	30 60 100 100 20	- - 300 -	-
Collector-Emitter Saturation	Voltage (Note 1)	$(I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc})$ $(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	V _{CE(sat)}	- -	0.4 0.75	Vdc
Base-Emitter Saturation Volta	age (Note 1)	$(I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc})$ $(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	V _{BE(sat)}	0.75 -	0.95 1.3	Vdc
SMALL-SIGNAL CHARACT	ERISTICS					
Current-Gain - Bandwidth Pi	oduct (I _C	= 20 mAdc, V _{CE} = 10 Vdc, f = 100 MHz)	f _T	200	_	MHz
Collector-Base Capacitance		$(V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C _{cb}	-	8.5	pF
Emitter-Base Capacitance		$(V_{EB} = 0.5 \text{ Vdc}, I_{C} = 0, f = 1.0 \text{ MHz})$	C _{eb}	-	30	pF
Input Impedance	(I _C	= 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{ie}	1.5 k	15 k	Ω
Voltage Feedback Ratio	(I _C	= 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{re}	0.1	8.0	X 10 ⁻⁴
Small-Signal Current Gain	(I _C	= 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{fe}	60	500	_
Output Admittance	(I _C	= 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{oe}	1.0	100	μmhos
SWITCHING CHARACTERIS	TICS					
Delay Time	$(V_{CC} = 30 \text{ Vdc}, V_{BE} = +2.0 \text{ Vdc},$ $I_{C} = 150 \text{ mAdc}, I_{B1} = 15 \text{ mAdc})$		t _d	-	15	ns
Rise Time			t _r	-	20	ns
Storage Time	(V _{CC} = 30 Vdc, I _C = 150 mAdc,		t _s	_	225	ns
Fall Time	$I_{B1} = 15 \text{ mA}, I_{B2} = 15 \text{ mA})$		t _f	_	30	ns

^{1.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

ORDERING INFORMATION

Device	Package	Shipping [†]
2N4403	TO-92	5000 Units / Bulk
2N4403G	TO-92 (Pb-Free)	5000 Units / Bulk
2N4403RLRA	TO-92	2000 / Tape & Reel
2N4403RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N4403RLRM	TO-92	2000 / Ammo Pack
2N4403RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N4403RLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

SWITCHING TIME EQUIVALENT TEST CIRCUIT

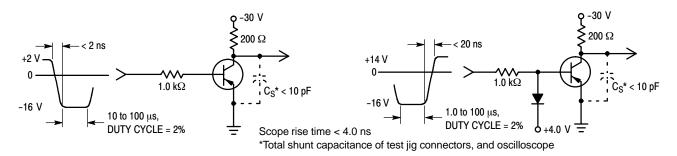


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

TRANSIENT CHARACTERISTICS

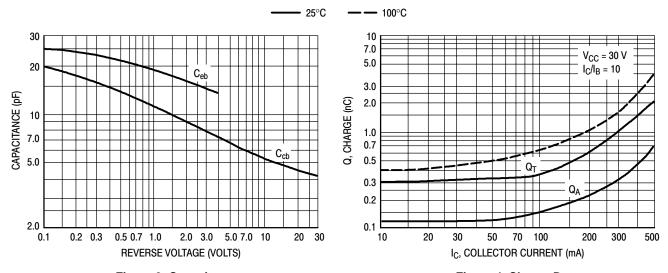
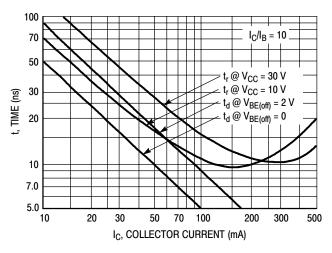


Figure 3. Capacitances

Figure 4. Charge Data



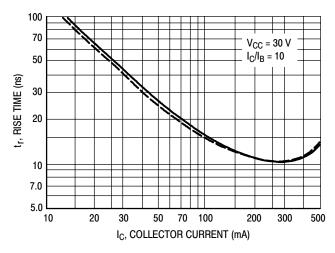


Figure 5. Turn-On Time

Figure 6. Rise Time

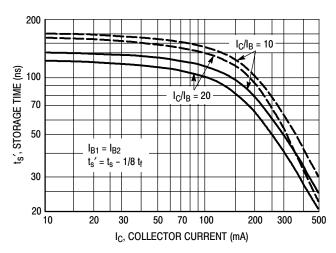
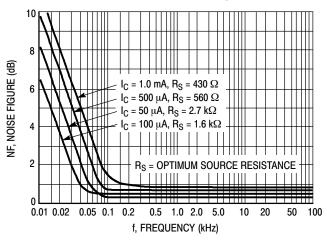
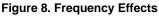


Figure 7. Storage Time

SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

 $V_{CE} = -10 \text{ Vdc}$, $T_A = 25^{\circ}\text{C}$; Bandwidth = 1.0 Hz





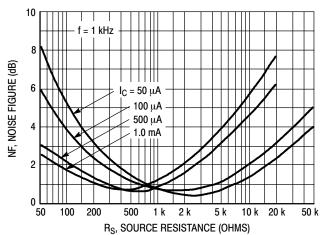


Figure 9. Source Resistance Effects

h PARAMETERS

 $V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz}, T_A = 25^{\circ}\text{C}$

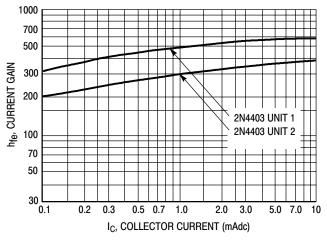
100 k

50

This group of graphs illustrates the relationship between $h_{\mbox{\scriptsize fe}}$ and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were selected from the 2N4403 lines, and the same units were used to develop the correspondingly-numbered curves on each graph.

2N4403 UNIT 1

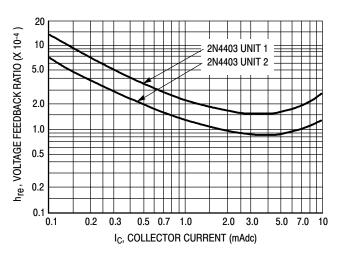
2N4403 UNIT 2



hie, INPUT IMPEDANCE (OHMS) 20 k 10 k 5 k 2 k 1 k 500 200 100 0.1 0.2 0.5 0.7 1.0 2.0 5.0 7.0

Figure 10. Current Gain

IC, COLLECTOR CURRENT (mAdc) Figure 11. Input Impedance



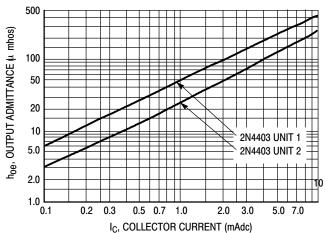


Figure 12. Voltage Feedback Ratio

Figure 13. Output Admittance

STATIC CHARACTERISTICS

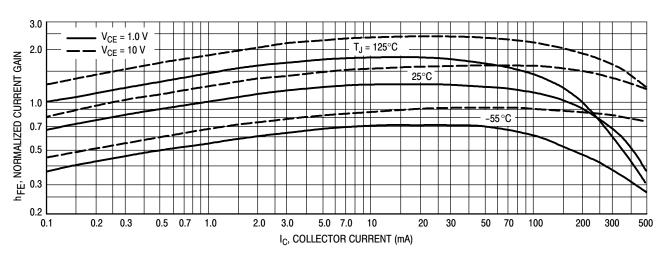


Figure 14. DC Current Gain

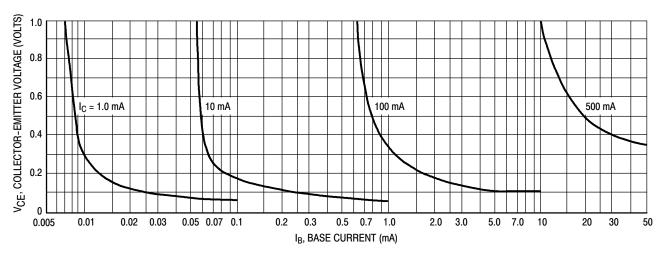


Figure 15. Collector Saturation Region

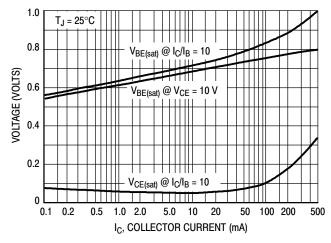


Figure 16. "On" Voltages

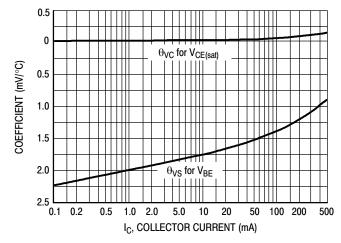
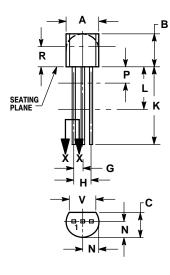


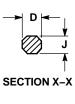
Figure 17. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**



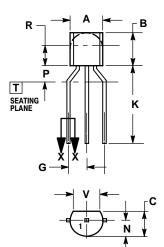
STRAIGHT LEAD **BULK PACK**



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION R IS UNCONTROLLED.

 LEAD DIMENSION IS UNCONTROLLED IN
- P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
٧	3.43		

PIN 1. EMITTER

BASE

COLLECTOR

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